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Thomas I. Wallow
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5 Accelerated Development of Materials and Processes: Joint Session with Conference 8681 and 8682
Clifford L. Henderson, Georgia Institute of Technology (United States)
Martha I. Sanchez, IBM Almaden Research Center (United States)

6 DSA Materials and Processing: Joint Session with Conference 8680 and 8682
Joy Y. Cheng, IBM Almaden Research Center (United States)
Ralph R. Dammel, AZ Electronic Materials USA Corporation (United States)

7 Negative Tone Patterning
Plamen Tzviatkov, FUJIFILM Electronic Materials U.S.A., Inc. (United States)
Scott W. Jessen, Texas Instruments Inc. (United States)

8 Novel Patterning Materials
Daniel P. Sanders, IBM Almaden Research Center (United States)
Ramakrishnan Ayothi, JSR Micro, Inc. (United States)

9 E-Beam Patterning Materials
Luisa D. Bozano, IBM Almaden Research Center (United States)
Roel Gronheid, IMEC (Belgium)

10 EUV Materials, Processing, and Analysis
Todd Ross Younkin, Intel Corporation (Belgium)
Roel Gronheid, IMEC (Belgium)

11 Fundamental Studies of RLS Behavior
Sean D. Burns, IBM Corporation (United States)
Douglas Guerrero, Brewer Science, Inc. (United States)